



INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: 150.00810102	Serial No.: 09/865,612
		Confirmation No. 4697
	Applicant(s): Brian A. Vaartstra	
	Filing Date: May 25, 2001	Group: 2823

U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	SubClass	Filing Date If Appropriate
G		5,015,747	05/14/91	Hostalek et al.			
G		5,036,022	07/30/91	Kuech et al.			
G		5,084,128	01/28/92	Baker			
G		5,112,432	5/1992	Erdmann et al.			
G		5,180,687	01/19/93	Mikoshiba et al.			
G		5,259,915	11/09/93	Pohl et al.			
G		5,384,289	01/24/95	Westmoreland et al.			
G		5,451,260	9/1995	Versteeg et al.			
G		5,545,591	08/13/96	Sugai et al.			
G		5,607,722	03/04/97	Vaartsrta et al.			
G		5,659,057	08/18/97	Vaartstra			
G		5,863,836	01/26/99	Jones			
G		5,924,012	07/13/99	Vaartstra			
G	X	6,244,575 B1	06/12/01	Vaartstra			
G	X	6,281,124 B1	08/28/01	Vaartstra			

FOREIGN PATENT DOCUMENTS

	Copy Enclosed	Document Number	Date	Country	Class	SubClass	Translation	
							Yes	No
G		DE 42 13 292 A1	10/28/93	Germany (translation attached)			X	
G		DD 295 876 A5	11/14/91	Germany (with English Language Abstract only)				X

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

G		Clabes et al., "Chemical reaction and Schottky-barrier formation at V/Si interfaces," <u>Physical Review B</u> , 29(4), 1540-1550 (1984).
G		Hostalek et al., "Novel Organometallic Starting Materials for Group III-V Semiconductor Metal-Organic Chemical Vapour Deposition," <u>Thin Solid Films</u> 174:1-4 (1989)

EXAMINER <i>FURSON</i>	Date Considered <i>11/30/02</i>
<small>*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>	

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		Leung et al., "Synthesis and structural characterisation of mono- and bi- nuclear cobalt(II) alkyls," <u>J. Chem. Soc. Dalton Trans.</u> 779-783 (1997)
G		Morgan et al., "A Surface EXAFS Study of the Vanadium/Si(111) Interface," <u>Surface Science</u> , 204, 428-444 (1988).
G		Remenyuk et al., "The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization," <u>Applied Surface Science</u> , 91, 352-354 (1995).
G		Scherer et al., "Amine-Stabilized Cyclopentadienyl Diisobutyl Aluminium Complexes as New Kinds of Precursors for the Deposition of Thin Aluminum Films by CVD," <u>Chem. Vap. Deposition</u> 3:33-35 (1997)
G		Schumann et al., "Intramolecularly Stabilized Organoaluminium, -gallium and -indium Derivatives/Crystal Structures of {o-[(Dimethylamino)methyl]phenyl} dimethylgallium and {o-[(Diethylamino)methyl]phenyl} dimethylindium," <u>Chem. Ber.</u> 123:2093-2099 (1990)
G		Singer, "Filling Contacts and Vias: A Progress Report," <u>Semiconductor Int'l</u> 89-90,92,94 (1996)
G		Van Koeten et al., "1, 4-Diaza- 1, 3-butadiene (α -Diimine) Ligands: Their Coordination Modes and the Reactivity of Their Metal Complexes," <u>Advances in Organometallic Chemistry</u> , 21, 151-239 (1982).
G		Versteeg et al., "Metalorganic Chemical Vapor Deposition by Pulsed Liquid Injection Using An Ultrasonic Nozzle: Titanium Dioxide on Sapphire from Titanium (IV) Isopropoxide," <u>J. of the American Ceramic Society</u> , 78, 2763-2768 (1995).

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